

Single Phase Rectifier Bridge

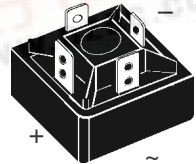
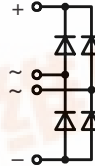
Standard and Avalanche Types

$$I_{dAV} = 18 \text{ A}$$

$$V_{RRM} = 800\text{-}1600 \text{ V}$$

V_{RSM} V	$V_{BRmin}^{①}$ V	V_{RRM} V	Standard Types	Avalanche Types
900		800	VBO 13-08NO2	
1300	1230	1200	VBO 13-12NO2	VBO 13-12AO2
1500	1430	1400	VBO 13-14NO2	VBO 13-14AO2
1700	1630	1600	VBO 13-16NO2	VBO 13-16AO2

① For Avalanche Types only



Symbol	Conditions	Maximum Ratings	Features
$I_{dAV}^{②}$	$T_C = 85^\circ\text{C}$, module	18 A	• Avalanche rated parts available
I_{dAVM}	module	30 A	• Package with DCB ceramic base plate
P_{RSM}	$T_{VJ} = T_{VJM}$ $t = 10 \mu\text{s}$	2.5 kW	• Isolation voltage 3600 V~
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	220 A	• Planar passivated chips
	$t = 10 \text{ ms}$ (50 Hz), sine	230 A	• Low forward voltage drop
	$t = 8.3 \text{ ms}$ (60 Hz), sine		• 1/4" fast-on terminals
	$T_{VJ} = T_{VJM}$ $t = 10 \text{ ms}$ (50 Hz), sine	180 A	• UL registered E 72873
	$V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	190 A	
I^2t	$T_{VJ} = 45^\circ\text{C}$ $t = 10 \text{ ms}$ (50 Hz), sine	240 A ² s	
	$V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	220 A ² s	
	$T_{VJ} = T_{VJM}$ $t = 10 \text{ ms}$ (50 Hz), sine	160 A ² s	
	$V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	150 A ² s	
T_{VJ}		-40...+150 °C	
T_{VJM}		150 °C	
T_{stg}		-40...+125 °C	
V_{ISOL}	50/60 Hz, RMS $t = 1 \text{ min}$	3000 V~	
	$I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	3600 V~	
M_d	Mounting torque (M5)	1.5-2 Nm	
	(10-32 UNF)	13-18 lb.in.	
Weight	typ.	15 g	

Features

- Avalanche rated parts available
- Package with DCB ceramic base plate
- Isolation voltage 3600 V~
- Planar passivated chips
- Low forward voltage drop
- 1/4" fast-on terminals
- UL registered E 72873

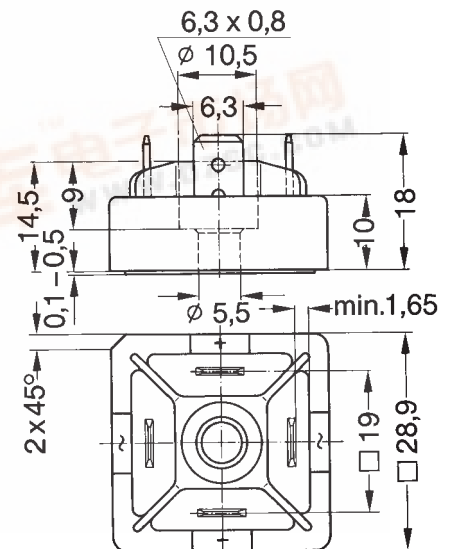
Applications

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Advantages

- Easy to mount with one screw
- Space and weight savings
- Improved temperature and power cycling

Dimensions in mm (1 mm = 0.0394")



Symbol	Test Conditions	Characteristic Values
I_R	$V_R = V_{RRM}$; $T_{VJ} = 25^\circ\text{C}$	$\leq 0.3 \text{ mA}$
	$V_R = V_{RRM}$; $T_{VJ} = T_{VJM}$	$\leq 5 \text{ mA}$
V_F	$I_F = 55 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	$\leq 1.8 \text{ V}$
V_{T0}	For power-loss calculations only	0.85 V
r_T	$T_{VJ} = T_{VJM}$	17 mΩ
R_{thJC}	per diode; DC current	5.6 K/W
	per module	1.4 K/W
R_{thJK}	per diode; DC current	6.0 K/W
	per module	1.5 K/W
d_s	Creeping distance on surface	13 mm
d_A	Creepage distance in air ③	9.5 mm
a	Max. allowable acceleration	50 m/s ²

Data according to IEC 60747 and refer to a single diode unless otherwise stated

② for resistive load at bridge output, ③ with isolated fast-on tabs.

IXYS reserves the right to change limits, test conditions and dimensions.

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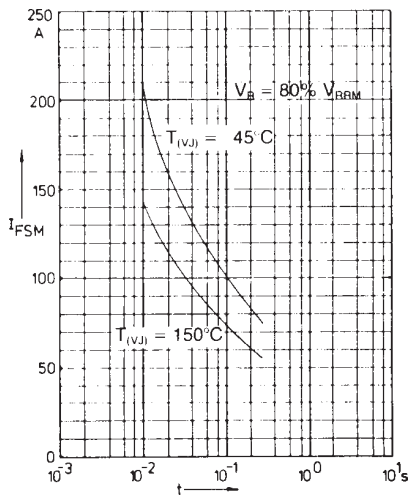


Fig. 1 Surge overload current per diode
 I_{FSM} : Crest value, t : duration

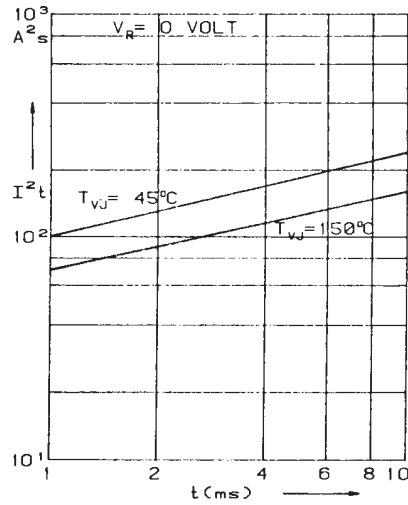


Fig. 2 I^2t versus time (1-10 ms)
per diode

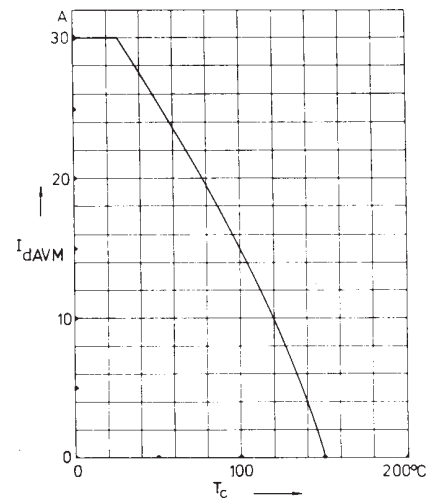


Fig. 3 Max. forward current at case temperature

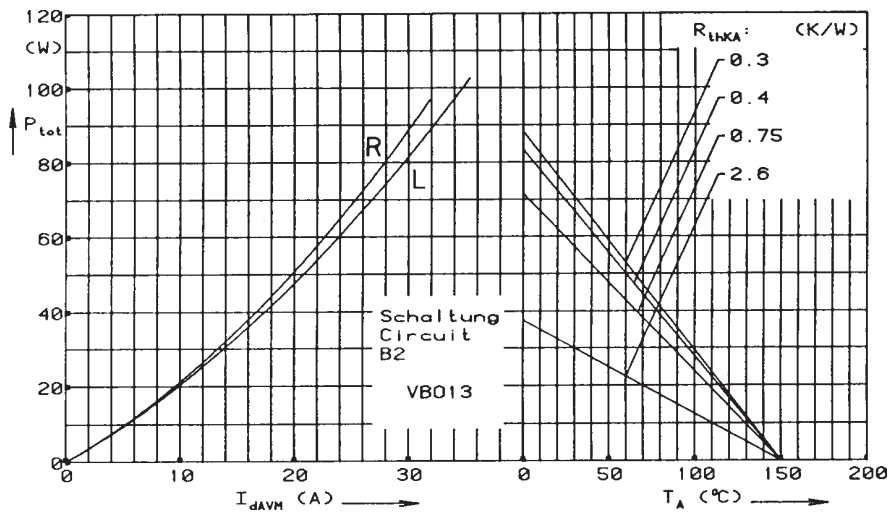


Fig. 4 Power dissipation versus direct output current and ambient temperature

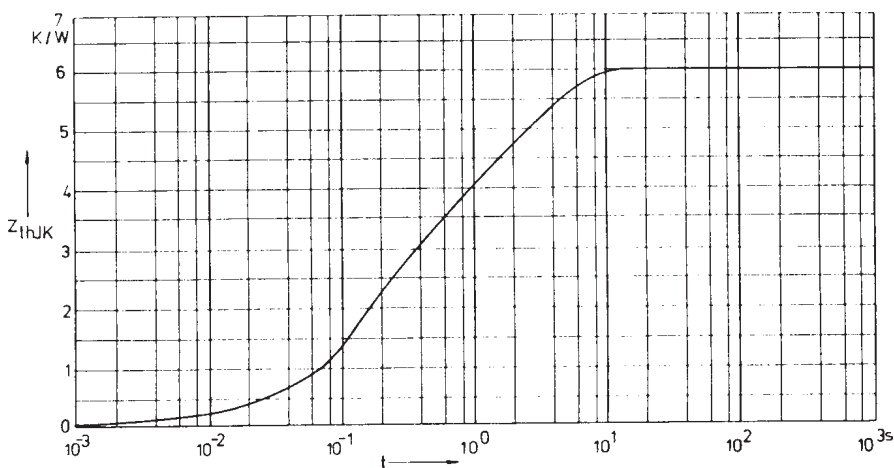


Fig. 5 Transient thermal impedance junction to heatsink per diode

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.059	0.00217
2	2.714	0.159
3	3.227	2.34